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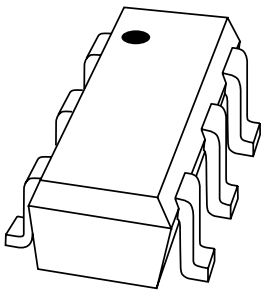
DATA SHEET



PUMB3

PNP resistor-equipped double transistor; R1 = 4.7 kΩ

Product specification

2001 Sep 19

Philips Semiconductors

PHILIPS

PNP resistor-equipped double transistor; R1 = 4.7 kΩ PUMB3

FEATURES

- Transistors with built-in bias resistor R1 (typ. 4.7 kΩ)
- No mutual interference between the transistors
- Simplification of circuit design
- Reduces number of components and board space.

APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

DESCRIPTION

PNP resistor-equipped double transistor in an SC-88 (SOT363) plastic package.

MARKING

TYPE NUMBER	MARKING CODE(1)
PUMB3	B5*

Note

1. * = p: Made in Hong Kong.
   * = t: Made in Malaysia.

PINNING

PIN	DESCRIPTION	
1, 4	emitter	TR1; TR2
2, 5	base	TR1; TR2
6, 3	collector	TR1; TR2

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	–50	V
I_{CM}	peak collector current	–100	mA
TR1	PNP	–	–
TR2	PNP	–	–
R1	bias resistor	4.7	kΩ

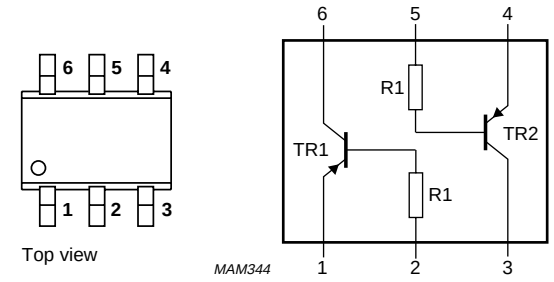


Fig.1 Simplified outline (SC-88; SOT363) and symbol.

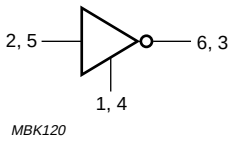


Fig.2 Equivalent inverter symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transistor					
V_{CBO}	collector-base voltage	open emitter	–	–50	V
V_{CEO}	collector-emitter voltage	open base	–	–50	V
V_{EBO}	emitter-base voltage	open collector	–	–10	V
V_I	input voltage				
	positive		–	+10	V
	negative		–	–40	V
I_O	output current (DC)		–	–100	mA
I_{CM}	peak collector current		–	–100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C; note 1	–	200	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C
Per device					
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C; note 1	–	300	mW

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	416	K/W

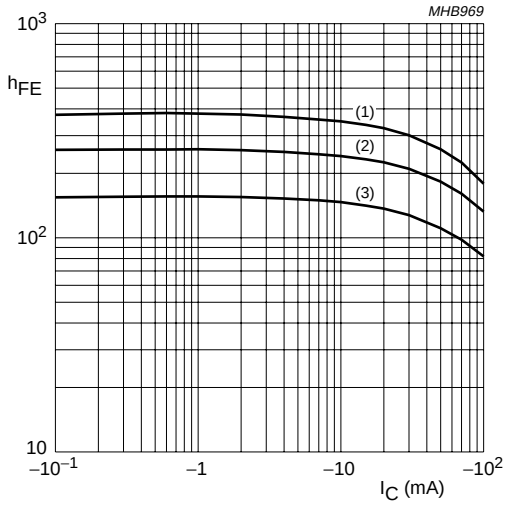
Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

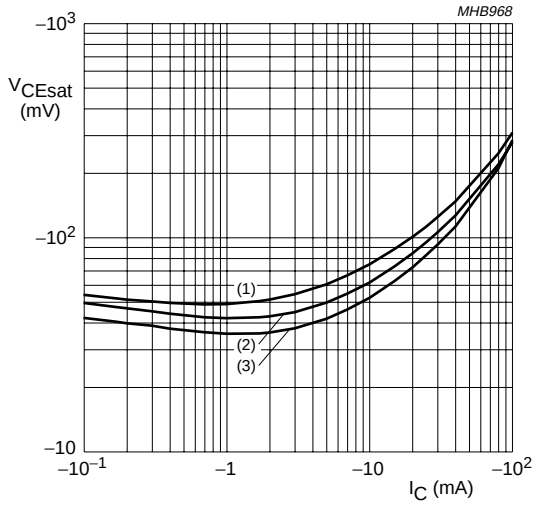
T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per transistor						
I_{CBO}	collector-base cut-off current	V_{CB} = –50 V; I_E = 0	–	–	–100	nA
I_{CEO}	collector-emitter cut-off current	V_{CE} = –30 V; I_B = 0	–	–	–1	µA
		V_{CE} = –30 V; I_B = 0; T_j = 150 °C	–	–	–50	µA
I_{EBO}	emitter-base cut-off current	V_{EB} = –5 V; I_C = 0	–	–	–100	nA
h_{FE}	DC current gain	V_{CE} = –5 V; I_C = –1 mA	200	–	–	
V_{CEsat}	saturation voltage	I_C = –5 mA; I_B = –0.25 mA	–	–	–100	mV
R_1	input resistor		3.3	4.7	6.1	kΩ
C_c	collector capacitance	$I_E = i_e$ = 0; V_{CB} = –10 V; f = 1 MHz	–	–	3	pF



V_{CE} = –5 V.
(1) T_{amb} = 100 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = –40 °C.

Fig.3 DC current gain as a function of collector current; typical values.

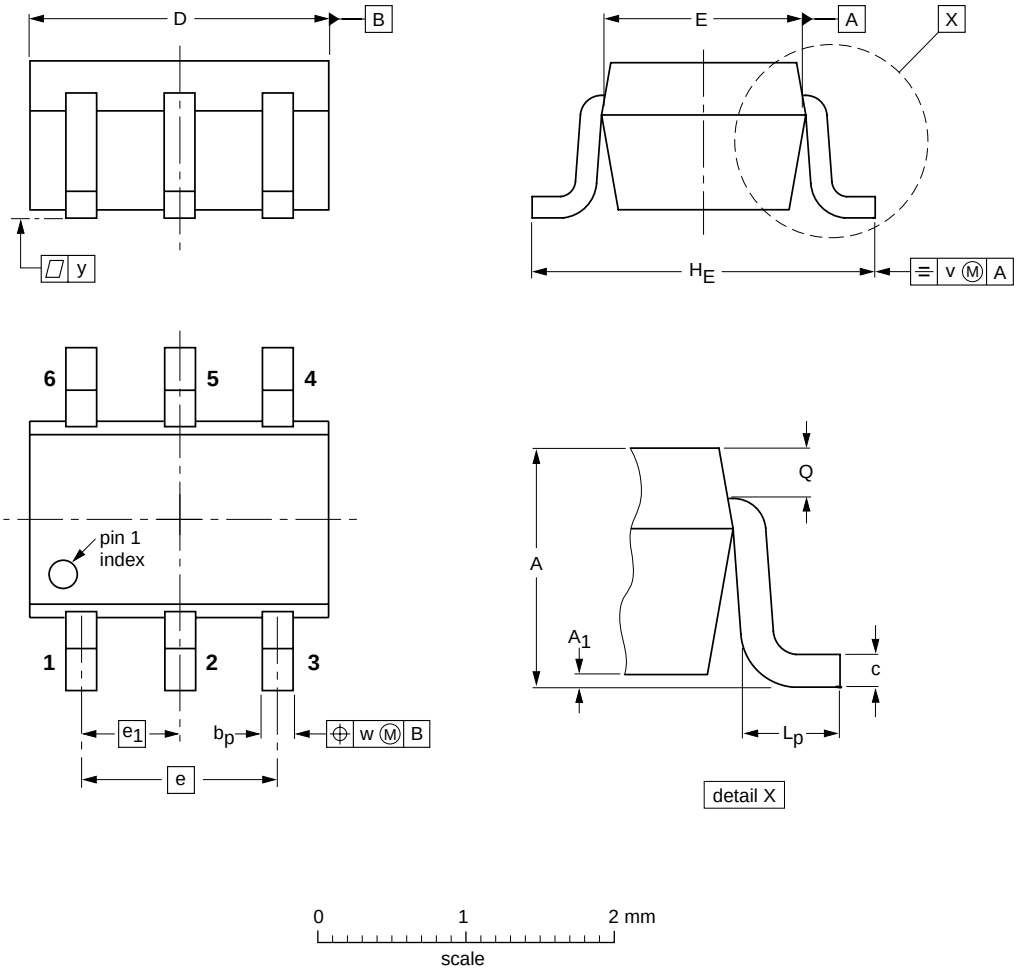


I_C/I_B = 20.
(1) T_{amb} = 100 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = –40 °C.

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.

PACKAGE OUTLINE

Plastic surface mounted package; 6 leads **SOT363**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT363			SC-88			97-02-28

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DATA SHEET STATUS[1]	PRODUCT STATUS[2]	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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